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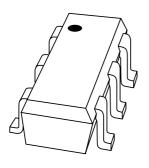
If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS

DATA SHEET



PBSS4240Y 40 V low V_{CEsat} NPN transistor

Product data sheet 2001 Jul 13



40 V low V_{CEsat} NPN transistor

PBSS4240Y

FEATURES

- Low collector-emitter saturation voltage
- · High current capability
- Improved device reliability due to reduced heat generation
- Replacement for SOT89/SOT223 standard packaged transistors due to enhanced performance.

APPLICATIONS

- · Supply line switching circuits
- · Battery management applications
- DC/DC converter applications
- · Strobe flash units
- Heavy duty battery powered equipment (motor and lamp drivers).

DESCRIPTION

NPN low V_{CEsat} transistor in a SOT363 (SC-88) plastic package.

PNP complement: PBSS5240Y.

MARKING

TYPE NUMBER	MARKING CODE(1)
PBSS4240Y	42*

Note

- 1. * = p: made in Hongkong.
 - * = t: made in Malaysia.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V_{CEO}	collector-emitter voltage	40	V
I _{CM}	peak collector current	3	Α
R _{CEsat}	equivalent on-resistance	<200	mΩ

PINNING

PIN	DESCRIPTION
1	collector
2	collector
3	base
4	emitter
5	collector
6	collector

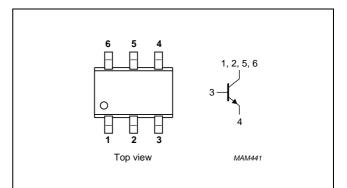


Fig.1 Simplified outline (SOT363; SC-88) and symbol.

40 V low V_{CEsat} NPN transistor

PBSS4240Y

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	40	V
V _{CEO}	collector-emitter voltage	open base	_	40	V
V _{EBO}	emitter-base voltage	open collector	_	5	V
I _C	collector current (DC)		_	2	Α
I _{CM}	peak collector current		-	3	Α
I _{BM}	peak base current		_	300	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	-	270	mW
		T _{amb} ≤ 25 °C; note 2	-	430	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Notes

- 1. Device mounted on a printed-circuit board, single side copper, tinplated and standard footprint.
- 2. Device mounted on a printed-circuit board, single side copper, tinplated and mounting pad for collector 1 cm².

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to	in free air; note 1	463	K/W
	ambient	in free air; note 2	291	K/W

Notes

- 1. Device mounted on a printed-circuit board, single side copper, tinplated and standard footprint.
- 2. Device mounted on a printed-circuit board, single side copper, tinplated and mounting pad for collector 1 cm².

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CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	V _{CB} = 30 V; I _E = 0	_	_	100	nA
		V _{CB} = 30 V; I _E = 0; T _j = 150 °C	_	_	50	μΑ
I _{EBO}	emitter-base cut-off current	V _{EB} = 4 V; I _C = 0	_	_	100	nA
h _{FE}	DC current gain	V _{CE} = 2 V; I _C = 100 mA	350	470	_	
		V _{CE} = 2 V; I _C = 500 mA	300	450	_	
		V _{CE} = 2 V; I _C = 1 A	300	420	_	
		V _{CE} = 2 V; I _C = 2 A	150	250	_	
V _{CEsat}	collector-emitter saturation	I _C = 100 mA; I _B = 1 mA	_	45	70	mV
	voltage	$I_C = 500 \text{ mA}; I_B = 50 \text{ mA}$	-	70	100	mV
		$I_C = 750 \text{ mA}; I_B = 15 \text{ mA}$	_	120	180	mV
		I _C = 1 A; I _B = 50 mA	-	130	180	mV
		I _C = 2 A; I _B = 200 mA	-	240	320	mV
R _{CEsat}	equivalent on-resistance	$I_C = 500 \text{ mA}$; $I_B = 50 \text{ mA}$; note 1	_	140	<200	mΩ
V _{BEsat}	base-emitter saturation voltage	I _C = 2 A; I _B = 200 mA	-	_	1.1	V
V _{BEon}	base-emitter turn-on voltage	V _{CE} = 2 V; I _C = 100 mA	_	_	0.75	V
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = I_e = 0; f = 1 \text{ MHz}$	_	15	20	pF
f _T	transition frequency	I _C = 100 mA; V _{CE} = 10 V; f = 100 MHz	100	230	_	MHz

Note

1. Pulse test: $t_p \leq 300~\mu s;~\delta \leq 0.02.$

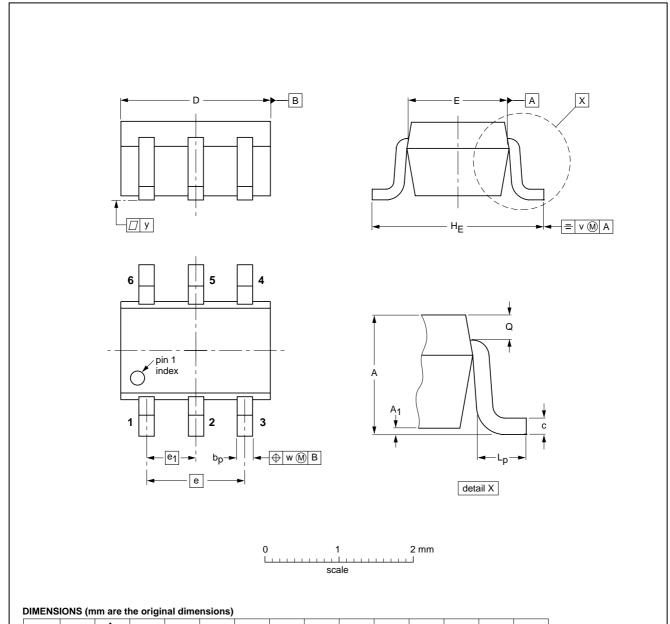
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PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT363



UNIT	A	A ₁ max	bp	С	D	E	е	e ₁	HE	Lp	Q	v	w	у
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

OUTLINE		REFER	RENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT363			SC-88			97-02-28

40 V low V_{CEsat} NPN transistor

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DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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NXP Semiconductors

Customer notification

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Printed in The Netherlands 613514/01/pp7 Date of release: 2001 Jul 13 Document order number: 9397 750 08385

